

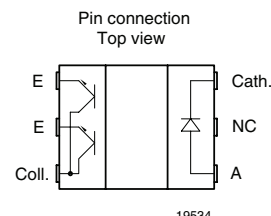
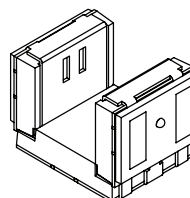
Subminiature Dual Channel Transmissive Optical Sensor with Phototransistor Outputs, RoHS Compliant, Released for Lead (Pb)-free Solder Process, AEC-Q101 Released

Description

The TCUT1300X01 is a compact transmissive sensor that includes an infrared emitter and two phototransistor detectors, located face-to-face in a surface mount package.

Features

- Product designed and qualified acc. AEC-Q101 for the automotive market
- Package type: surface mount
- Detector type: phototransistor
- Dimensions:
L 5.5 mm x W 4 mm x H 4 mm
- Gap: 3 mm
- Aperture: 0.3 mm
- Channel distance (center to center): 0.8 mm
- Typical output current under test: $I_C = 0.6$ mA
- Emitter wavelength: 950 nm
- Lead (Pb)-free soldering released
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC
- Minimum order quantity: 2000 pcs, 2000 pcs/reel



Applications

- Automotive optical sensors
- Accurate position sensor for encoder
- Sensor for motion, speed and direction

Absolute Maximum Ratings

$T_{amb} = 25$ °C, unless otherwise specified

Coupler

Parameter	Test condition	Symbol	Value	Unit
Power dissipation	$T_{amb} \leq 25$ °C	P	150	mW
Ambient temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	in accordance with fig. 15	T_{sd}	260	°C

Input (Emitter)

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	25	mA
Forward surge current	$t_p \leq 10$ μ s	I_{FSM}	200	mA
Power dissipation	$T_{amb} \leq 25$ °C	P_V	75	mW

Output (Detector)

Parameter	Test condition	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	20	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	20	mA
Power dissipation	$T_{amb} \leq 25$ °C	P_V	75	mW

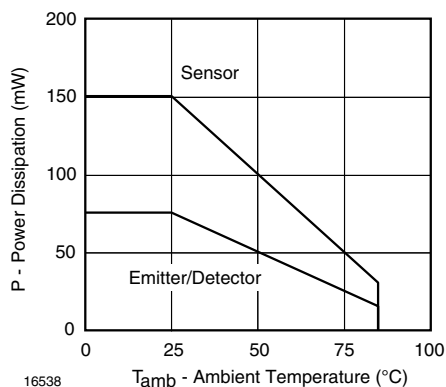


Figure 1. Power Dissipation Limit vs. Ambient Temperature

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Coupler

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector current per channel	V _{CE} = 5 V, I _F = 15 mA	I _C	300	600		μA
Collector emitter saturation voltage	I _F = 15 mA, I _C = 0.05 mA	V _{CEsat}			0.4	V

Input (Emitter)

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I _F = 15 mA	V _F		1.2	1.4	V
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz	C _j		25		pF

Output (Detector)

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector emitter voltage I _C	I _C = 1 mA	V _{CEO}	20			V
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V
Collector dark current	V _{CE} = 25 V, I _F = 0, E = 0	I _{CEO}		1	100	nA

Switching Characteristics

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Rise time	I _C = 0.3 mA, V _{CE} = 5 V, R _L = 100 Ω (see figure 2)	t _r		20.0	150	μs
Fall time	I _C = 0.3 mA, V _{CE} = 5 V, R _L = 100 Ω (see figure 2)	t _f		30.0	150	μs

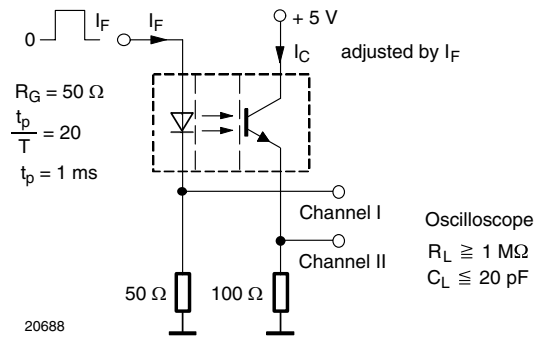


Figure 2. Test Circuit for t_r and t_f

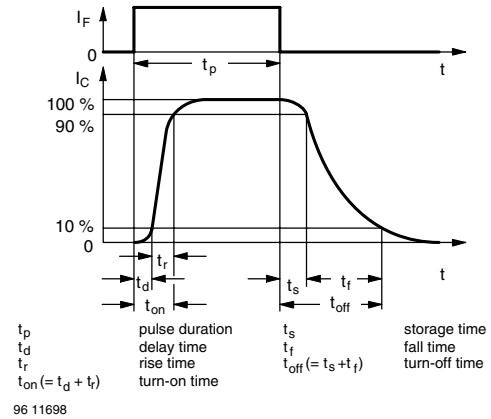


Figure 3. Switching Times

Typical Characteristics

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

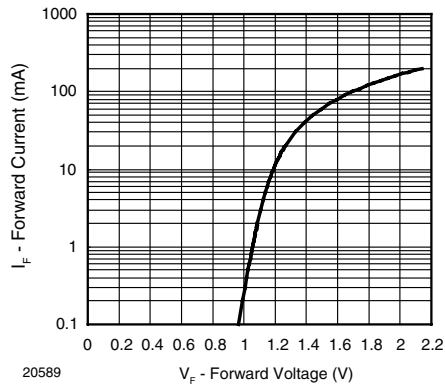


Figure 4. Forward Current vs. Forward Voltage

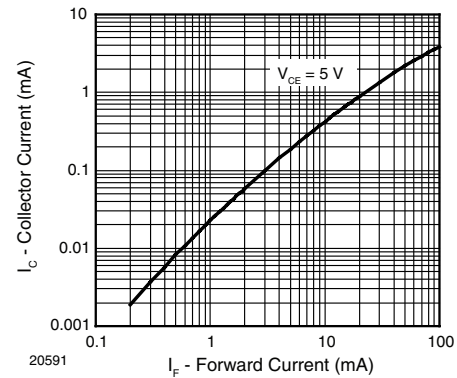


Figure 6. Collector Current vs. Forward Current

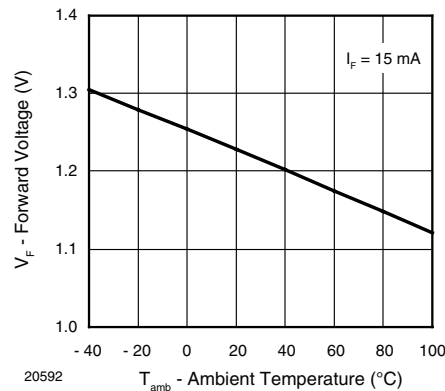


Figure 5. Forward Voltage vs. Ambient Temperature

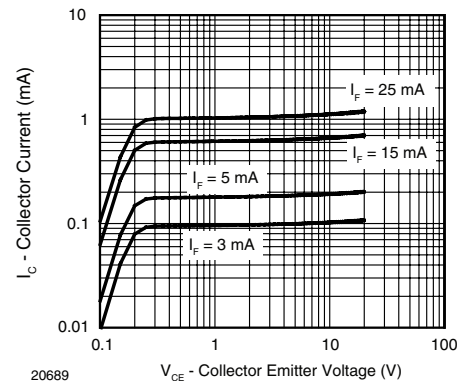


Figure 7. Collector Current vs. Collector Emitter Voltage

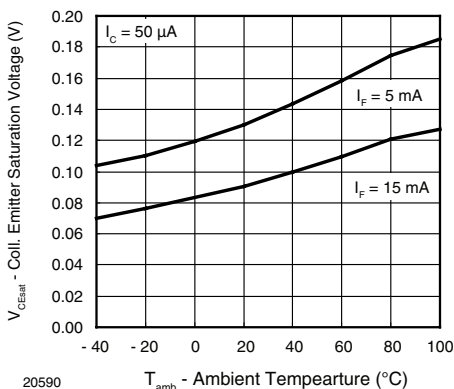


Figure 8. Collector Emitter Saturation Voltage vs. Ambient Temperature

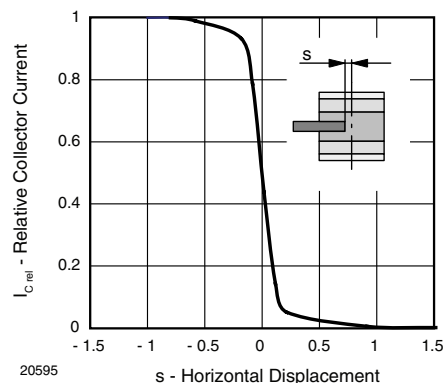


Figure 11. Relative Collector Current vs. Horizontal Displacement

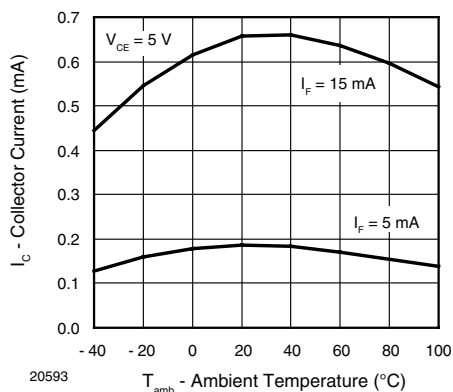


Figure 9. Collector Current vs. Ambient Temperature

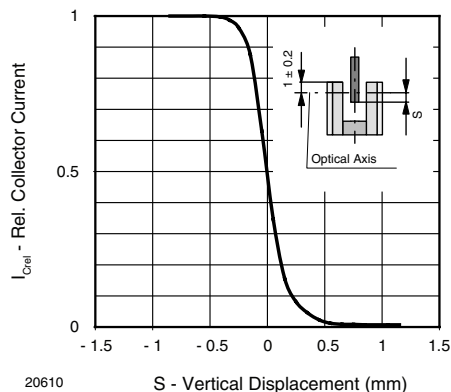


Figure 12. Relative Collector Current vs. Vertical Displacement

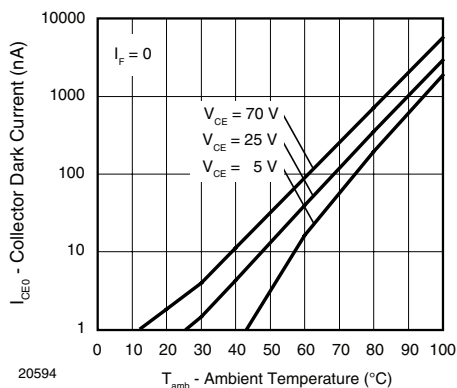


Figure 10. Collector Dark Current vs. Ambient Temperature

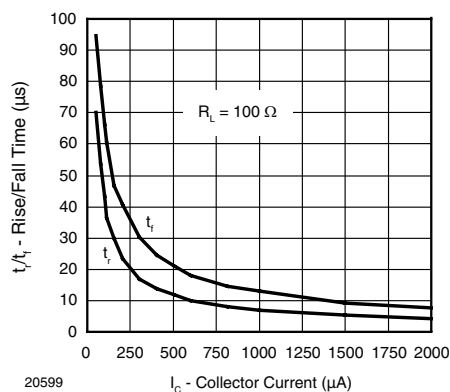


Figure 13. Rise/Fall Time vs. Collector Current

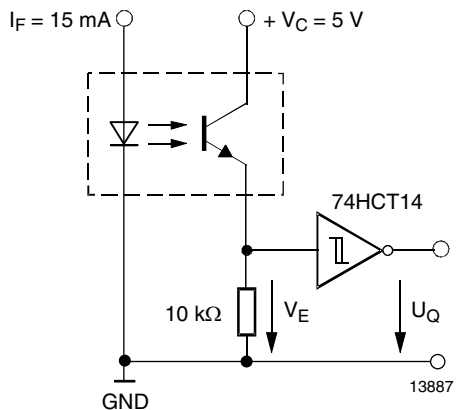


Figure 14. Application example

Floor Life

Level 1, acc. JEDEC, J-STD-020. No time limit.

Reflow Solder Profile

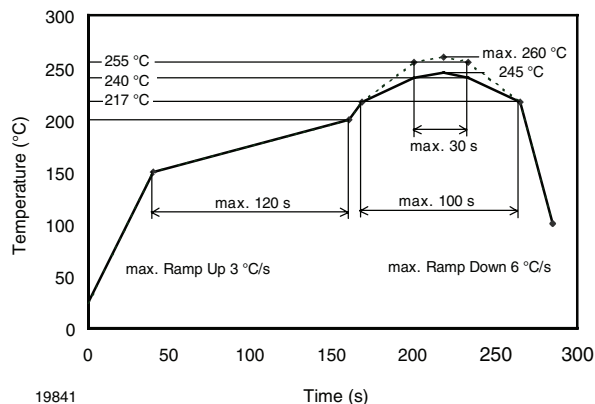
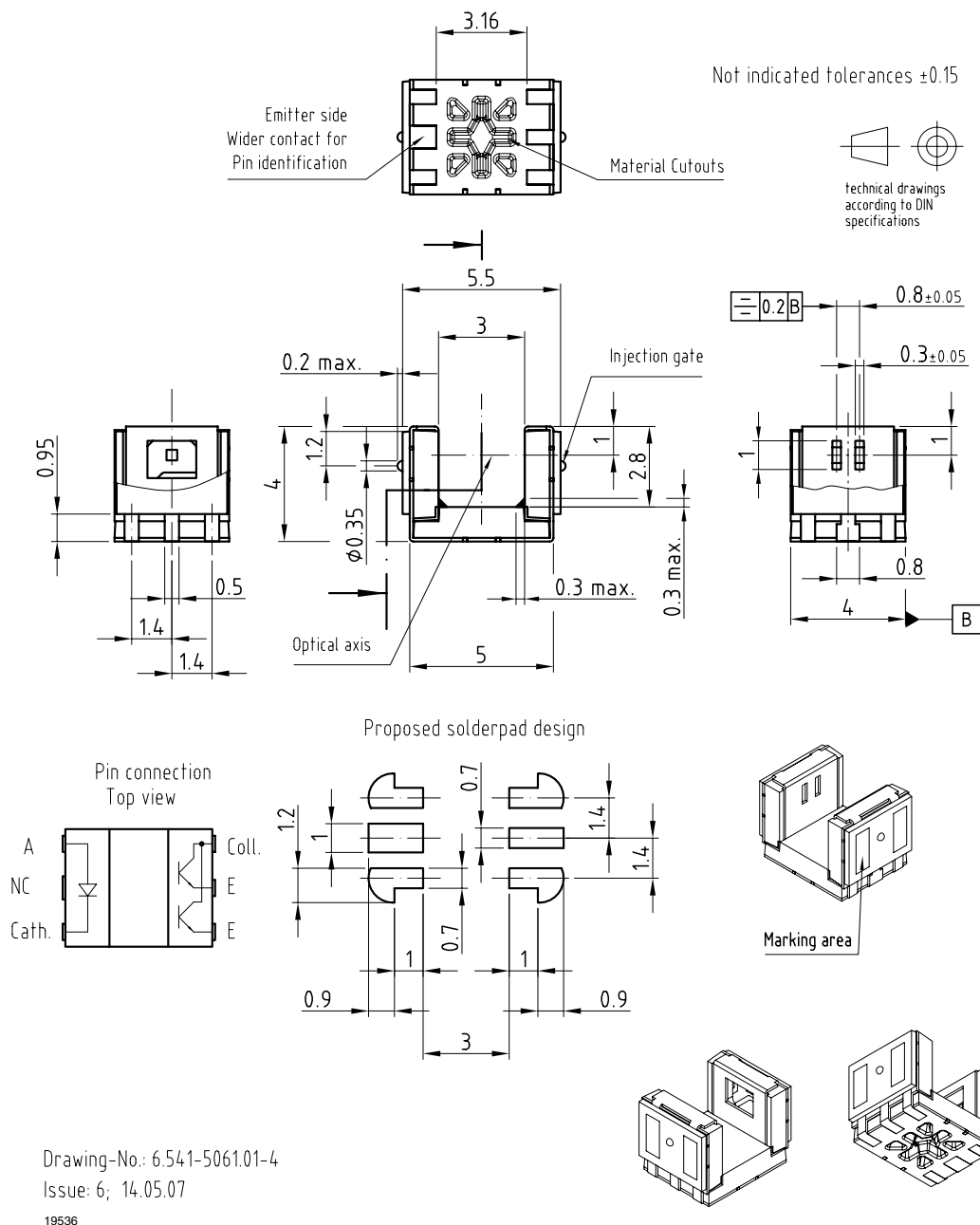


Figure 15. Lead (Pb)-free Reflow Solder Profile acc. J-STD-020C

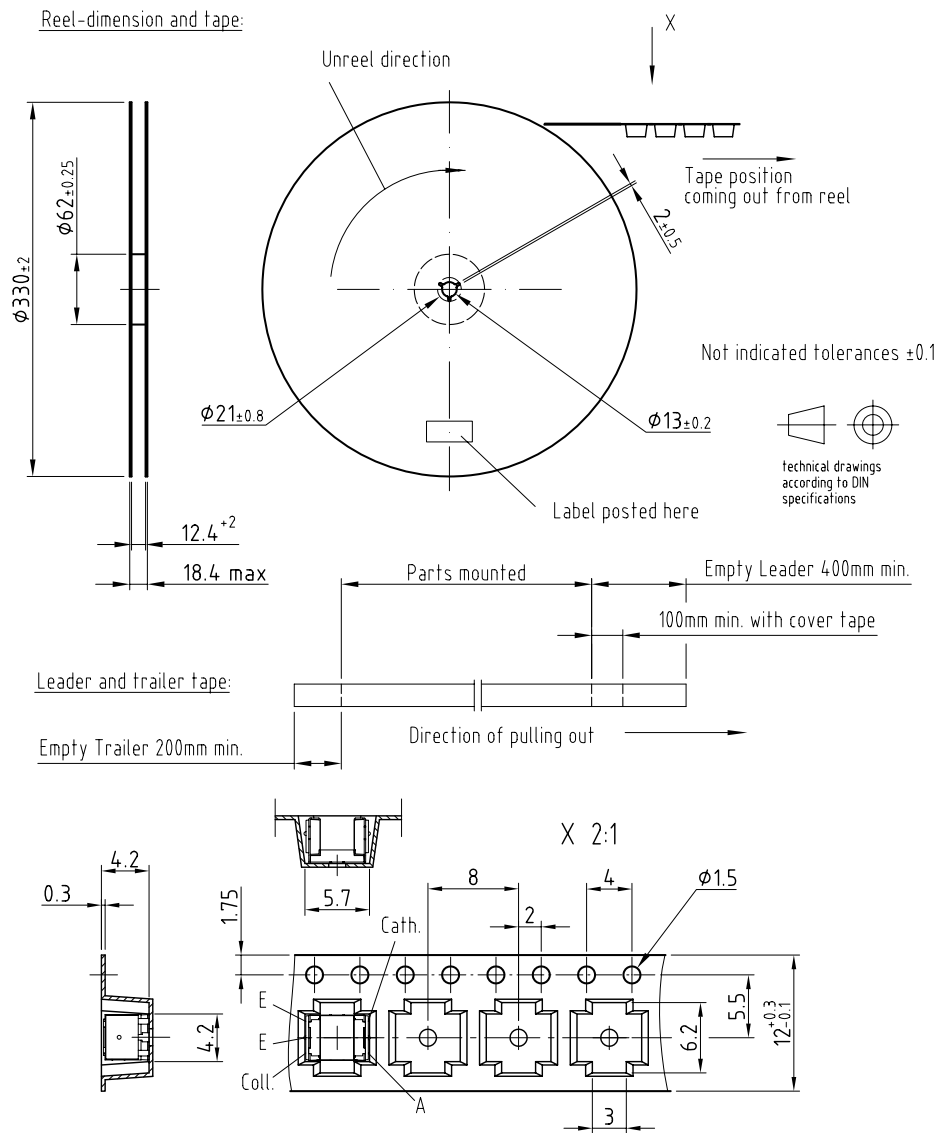
Reliability Tests in Reference to AEC-Q101 Release

Test	Condition	Duration	Lot Size - Rejects
High temperature storage	$T_{stg(max)} = 100\text{ }^{\circ}\text{C}$	1000 h	3 x 50 pcs - 0 pcs
Low temperature storage	$T_{stg(min)} = -40\text{ }^{\circ}\text{C}$	1000 h	3 x 50 pcs - 0 pcs
Temperature cycling	$-40\text{ }^{\circ}\text{C}/+100\text{ }^{\circ}\text{C}$	1000 x	3 x 77 pcs - 0 pcs
H3TRB	85 °C/85 % RH, Emitters: $V_R = 4\text{ V}$, detectors: $V_{CEO} = 5\text{ V}$	1000 h	3 x 77 pcs - 0 pcs
Intermittent operational life	Emitters: $I_F = 80\text{ mA DC}$, detectors: $V_{CE} = 16\text{ V}$, duty cycle: 2 min on, 2 min off, $T_{amb} = 25\text{ }^{\circ}\text{C}$	1000 h (15000 cycles)	3 x 77 pcs - 0 pcs

Package Dimensions in millimeters



Package Dimensions in millimeters



Drawing-No.: 9.800-5092.01-4

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20611

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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